# MSKSEMI 美森科













**ESD** 

TV

TSS

MOV

GDT

 $\mathsf{PLED}$ 

MS8515

Product specification





### Ultra Low Noise Rail-to-Rail I/O CMOS Precision OPERATIONAL AMPLIFIERS

#### **GENERAL DESCRIPTION**

The MS8515 family represents a newgener ation of low-noise operational amplifiers,offering o utstanding dc precision and acperformance.Rai-to-Rail input and output,lowoffset (2µV),low noise(6 nVNHz),quiescentcurrent of 600 µA,and a 6-MHz bandwidthmake this part very attractive for a variety ofprecision and portable applications

In addition, this device has a reasonably widesup ply range(2V to 5.5V) with excellent PSRR making it attractive for applications that rundirectly from batteries without regulation.

The MS8515 (single),MS8515 (dual)and MS8515 (quad)families of operational amplifiers are specified for operation from-25  $^{\circ}$  to+125  $^{\circ}$ .

#### **FEATURES**

- Input Offset Voltage:2μV (Typical)
- Zero Drift:0.03µV/C (Typical)
- Ultra Low Noise:6nV/VHz at 1kHz
- Supply Range:2V to 5.5V
- Gain Bandwidth:6 MHz
- Slew rate:5V/us
- Quiescent current:600µA (Vs=5V)
- Rail-to-Rail Input and Output
- Micro size Packages:
   MS8515ARTZ:SOT-23-5
   MS8515AKSZ:SC70-5

#### **APPLICATIONS**

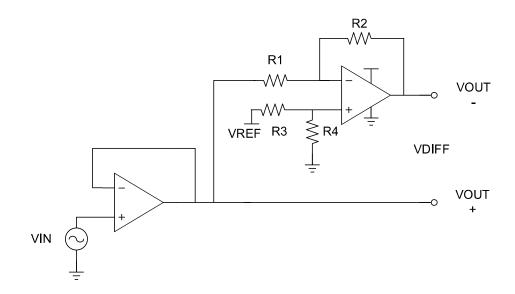
- ADC Buffer
- Audio Equipment
- Medical Instrumentation
- Handheld Test Equipment
- Active Filtering
- Sensor Signal Conditioning

#### **Reference News**

MODEL	Op Temp(℃)	PACKAGE	OUTLINE	Marking	Minimum packaging (PCS)
MS8515ARTZ	-25℃~125℃	SOT-23-5		• BDA	3000
MS8515AKSZ	<b>-25℃~125℃</b>	SC70-5		• BDA	3000

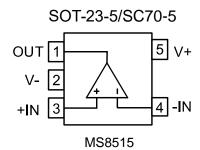


#### **TYPICAL APPLICATION**



**Figure 1.Typical Application** 

### Pin Configuration and Functions (Top View) Pin Description



PIN		I/0	DESCRIPTION	
NAME	Number		DESCRIF I TON	
+IN	3	l	Positive (noninverting)input	
-IN	4	l	Negative(inverting)input	
OUT	1	0	Output	
V-	2	_	Positive(highest)power supply	
V+	5	_	Negative(lowest)power supply	



#### **SPECIFICATIONS**

#### Absolute Maximum Ratings(1)

		MIN	MAX	UNIT
	Supply Voltage		6	V
Voltage	Signal Input Terminals Voltage <sup>(2)</sup>	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Voltage <sup>(3)</sup>	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Current <sup>(2)</sup>	-10	10	mA
Current	Signal output Terminals Current <sup>(3)</sup>	<b>-</b> 200	200	mA
	Output Short-Circuit <sup>(4)</sup>	Cont	inuous	
	Operating Temperature Range	<b>-</b> 25	125	°C
$\theta_{JA}$	Storage Temperature Range	<b>-</b> 65	150	°C
	Junction Temperature	-40	150	°C

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) Input terminals are diode clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current limited to 10mA or less.
- (3) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±200mA or less.
- (4) Short-circuit to ground, one amplifier per package.

#### **ESD Ratings**

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-Body Model (HBM)	±4000	V
		Charged-Device Model (CDM)	±500	V
		Machine Model	100	>

#### **Recommended Operating Conditions**

		MIN	MAX	UNIT
Supply voltage,	Single-supply	2	5.5	V
Vs= (V+) - (V-)	Dual-supply	±1	±2.75	V



#### **ELECTRICAL CHARACTERISTICS(V<sub>S</sub> = +5V)**

At  $T_A = 25$ °C,  $V_{CM}=V_{OUT}=V_S/2$ , unless otherwise noted.

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET	VOLTAGE					
Vos	Input Offset Voltage			2	10	μV
dV <sub>OS</sub> /dT	Input Offset Voltage Average Drift	T <sub>A</sub> = -25°C to 125°C		0.03		μV/°C
INPUT C	URRENT					
В	Input Bias Current			500		pА
los	Input Offset Current			50		pА
NOISE						
$V_N$	Input Voltage Noise	f=0.1Hz to 10Hz		0.3		μV <sub>PP</sub>
<b>e</b> n	Input Voltage Noise Density	f=1kHz		6		nV/√Hz
INPUT V	OLTAGE					
V <sub>см</sub>	Common-Mode Voltage Range		V <sub>S</sub> 0.1		V <sub>S+</sub> +0.1	V
CMRR	Common-Mode Rejection Ratio	V <sub>CM</sub> =0.1V to 4V	110	130		dB
FREQUE	NCY RESPONSE					
GBW	Gain-Bandwidth Product	C <sub>L</sub> =100pF		6		MHz
SR	Slew Rate	G = +1, V <sub>IN</sub> =2V Step		5		V/us
ts	Settling Time to 0.1%	G = +1, V <sub>IN</sub> =2V Step		0.7		us
THD+N	Total Harmonic Distortion +Noise	G=1, $V_O$ =1 $V_{RMS}$ , f=1kHz, $R_L$ =10k $\Omega$		0.0004		%
OUTPUT						
Av	Open-Loop Voltage Gain	$V_{OUT}$ =0.1V to 4.9V $R_L$ =10k $\Omega$	135	150		dB
V <sub>он</sub>	High output voltage swing	R <sub>L</sub> =10kΩ		10	20	mV
<b>V</b> OH	Trigit output voltage swilly	R <sub>L</sub> =2kΩ		50	60	mV

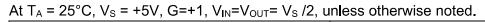


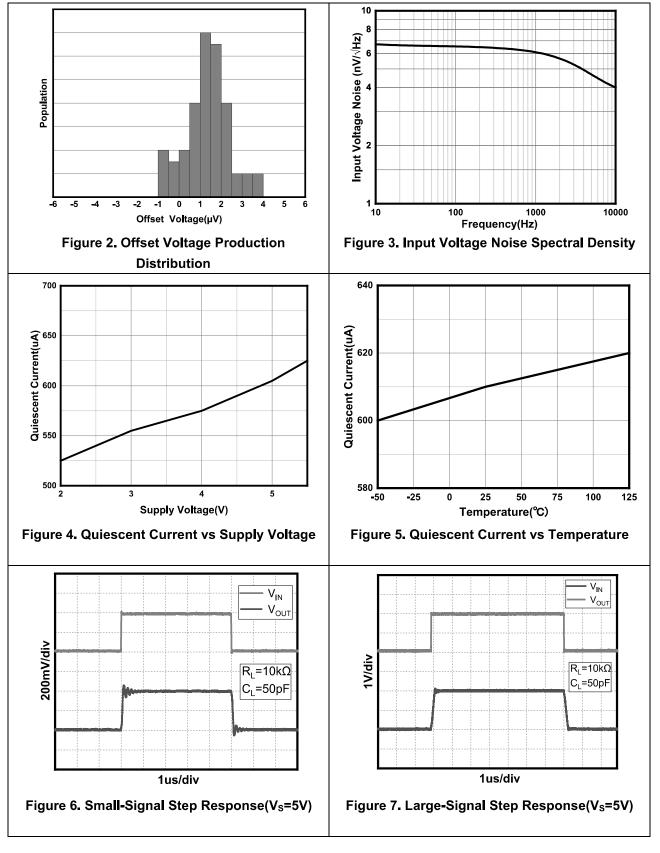
		R <sub>L</sub> =10kΩ		10	20	mV
V <sub>OL</sub>	Low output voltage swing	R <sub>L</sub> =2kΩ		35	45	mV
1	Output Short-Circuit	Source current		30		mA
Isc	Current	Sink current		65		mA
C <sub>L</sub> <sup>(1)</sup>	Capacitive Load Drive	G = +1, V <sub>IN</sub> =0.2V Step			560	pF
POWER	SUPPLY					
PSRR	Power-Supply Rejection Ratio	V <sub>S</sub> =1.5V to 5.5V	110	130		dB
Vs	Operating Voltage Range		2		5.5	V
IQ	Quiescent Current/Amplifier	I <sub>O</sub> =0A		600	700	uA

<sup>(1)</sup> Capacitive load drive means that above a given maximum value, the output waveform will oscillate under the step response.



#### **TYPICAL CHARACTERISTICS**



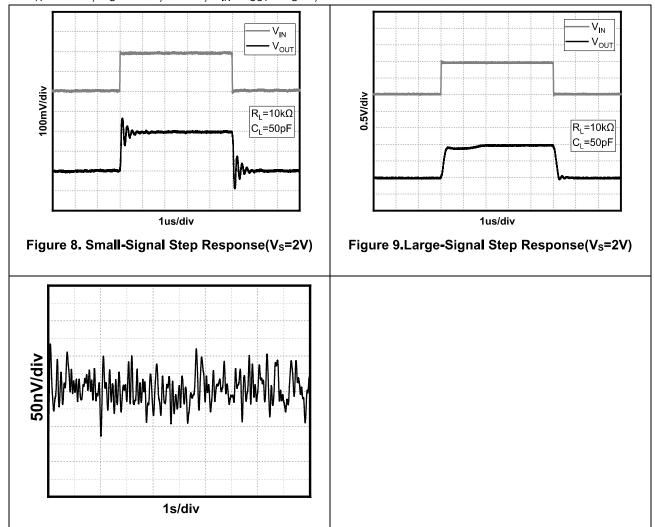




#### **TYPICAL CHARACTERISTICS**

Figure 10. 0.1Hz to 10Hz Noise

At  $T_A = 25$ °C,  $V_S = +5V$ , G=+1,  $V_{IN}=V_{OUT}=V_S/2$ , unless otherwise noted.





#### **Detailed Description**

#### Oyerview

The MS8515 devices are a low noise,unity-gain stable,rai-to-rail precision operational amplifier that operate in a single-supply voltage range of 2V to 5.5V(±1V to±2.75V). A high supply voltage of 6V(absolute maximum)can permanently damage the amplifier. Rail-to-rail input and output wobbles significantly increase the dynamic range ,especially in low-supply applications. Good layout practices require that a 01uF capacitor be used where it is tightly threaded through the power supply pin.

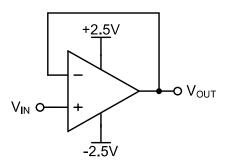
#### **Phase Reversal Protection**

The MS8515 devices have internal phase-reversal protection. Many op amps exhibit phase reversal when the input is driven beyond the linear common-mode rang e. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the MS8515 prevents phase reversal with excessive common-mode voltage. Instead, the appropriate rail limits the output voltage.

#### **Typical Applications**

#### 1 Voltage Follower

As shown in Figure 11,the voltage gain is 1. With this circuit, the output voltage Vour is configured to be equal to the input voltage Viw. Due to the high input impedance and low output impedance, the circuit can also stabilize the output voltage, the output voltage expression is



#### 2 Inverting Proportional Amplifier

As shown in Figure 12, for a reverse-phase proportional amplifier, the input voltage Vin is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage Vour is inversely with the input voltage Vin. The input impedance of the circuit is equal to R1, and the output voltage expression is

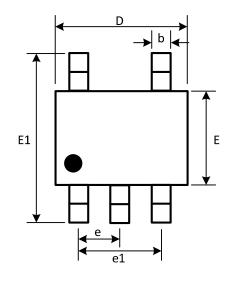
(2)

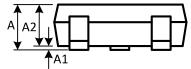
$$V_{OUT} = \frac{R2}{R1} V_{IN}$$

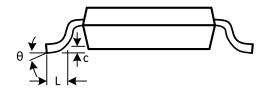


#### **PACKAGE DESCRIPTION**

#### SOT23-5





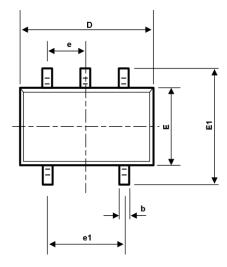


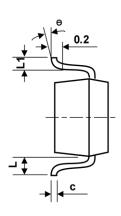
(Unit: mm)

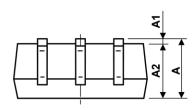
Symbol	Min	Max
А	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
С	0.100	0.200
D	2.820	3.020
е	0.950	(BSC)
e1	1.800	2.000
E	1.500	1.700
E1	2.650	2.950
L	0.300	0.600
θ	0°	8°



## Package Outline SC70-5







aymhal	Dimension I	n Millimeters	Dimension	ions In Inches	
symbol	Min	Max	Min 0.035 0.000 0.035 0.006 0.004 0.079 0.045 0.085	Max	
А	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.110	0.175	0.004	0.007	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650	TYP	0.02	6TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525	REF	0.02	1REF	
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	



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